

TRADEMARK ASSIGNMENT COVER SHEET

Electronic Version v1.1
Stylesheet Version v1.2

ETAS ID: TM608108

SUBMISSION TYPE:	NEW ASSIGNMENT		
NATURE OF CONVEYANCE:	INTELLECTUAL PROPERTY SECURITY AGREEMENT		
CONVEYING PARTY DATA			
Name	Formerly	Execution Date	Entity Type
NANTERO, INC.		11/10/2020	Corporation: DELAWARE
RECEIVING PARTY DATA			
Name:	Silicon Valley Bank		
Street Address:	275 Grove Street, Suite 2-200		
City:	Newton		
State/Country:	MASSACHUSETTS		
Postal Code:	02466		
Entity Type:	Corporation: CALIFORNIA		
PROPERTY NUMBERS Total: 6			
Property Type	Number	Word Mark	
Registration Number:	3720099	ENRAM	
Registration Number:	3723784	NANOLOGIC	
Registration Number:	3127237	NANTERO	
Registration Number:	4151679	NRAM	
Registration Number:	5377792	NTDF	
Registration Number:	5377794	NTSL	
CORRESPONDENCE DATA			
Fax Number:			
<i>Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.</i>			
Phone:	2023704750		
Email:	ipteam@cogencyglobal.com		
Correspondent Name:	Jennifer Tindie		
Address Line 1:	1025 Vermont Ave NW, Suite 1130		
Address Line 2:	COGENCY GLOBAL INC.		
Address Line 4:	Washington, D.C. 20005		
ATTORNEY DOCKET NUMBER:	1288173 TM		
NAME OF SUBMITTER:	Sarah Mackin		
SIGNATURE:	/Sarah Mackin/		
DATE SIGNED:	11/11/2020		

OP \$165.00 3720099

Total Attachments: 43

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INTELLECTUAL PROPERTY SECURITY AGREEMENT

This Intellectual Property Security Agreement (this “Agreement”) is entered into as of November 10, 2020, by and between **SILICON VALLEY BANK**, a California corporation, with a loan production office located at 275 Grove Street, Suite 2-200, Newton, Massachusetts 02466 (“Bank”) and **NANTERO, INC.**, a Delaware corporation with its principal place of business located at 25-B Olympia Avenue, Woburn, Massachusetts 01801 (“Grantor”).

RECITALS

A. Bank has agreed to make certain advances of money and to extend certain financial accommodations to Grantor (the “Loans”) in the amounts and manner set forth in that certain Loan and Security Agreement by and between Bank and Grantor dated as of May 10, 2018, as amended by that certain First Amendment to Loan and Security Agreement dated as of April 26, 2019 by and between Bank and Grantor, as effected by that certain Deferral Agreement dated as of April 2, 2020 by and between Bank and Grantor, and as further amended by that certain Second Amendment to Loan and Security Agreement between Bank and Grantor dated as of the date hereof (as the same has been and as may be further amended, modified or supplemented from time to time, the “Loan Agreement”; capitalized terms used herein are used as defined in the Loan Agreement). Bank is willing to make the Loans to Grantor, but only upon the condition, among others, that Grantor shall grant to Bank a security interest in its Copyrights, Trademarks, Patents, and Mask Works (as each term is described below) to secure the obligations of Grantor to Bank.

B. Pursuant to the terms of the Loan Agreement, Grantor has granted to Bank a security interest in all of Grantor’s right, title and interest, whether presently existing or hereafter acquired, in, to and under all of the Collateral.

NOW, THEREFORE, for good and valuable consideration, receipt of which is hereby acknowledged, and intending to be legally bound, as collateral security for the prompt and complete payment when due of Grantor’s obligations to Bank, Grantor hereby represents, warrants, covenants and agrees as follows:

AGREEMENT

1. Grant of Security Interest. To secure Grantor’s obligations to Bank, Grantor grants and pledges to Bank a security interest in all of Grantor's right, title and interest in, to and under its intellectual property (all of which shall collectively be called the “Intellectual Property Collateral”), including, without limitation, the following:

(a) Any and all copyright rights, copyright applications, copyright registrations and like protections in each work of authorship and derivative work thereof, whether published or unpublished and whether or not the same also constitutes a trade secret, now or hereafter existing, created, acquired or held, including without limitation those set forth on Exhibit A attached hereto (collectively, the “Copyrights”);

(b) Any and all trade secrets, and any and all intellectual property rights in computer software and computer software products now or hereafter existing, created, acquired or held;

(c) Any and all design rights that may be available to Grantor now or hereafter existing, created, acquired or held;

(d) All patents, patent applications and like protections including, without limitation, improvements, divisions, continuations, renewals, reissues, extensions and continuations-in-part of the same, including without limitation the patents and patent applications set forth on Exhibit B attached hereto (collectively, the "Patents");

(e) Any trademark and servicemark rights, whether registered or not, applications to register and registrations of the same and like protections, and the entire goodwill of the business of Grantor connected with and symbolized by such trademarks, including without limitation those set forth on Exhibit C attached hereto (collectively, the "Trademarks");

(f) All mask works or similar rights available for the protection of semiconductor chips, now owned or hereafter acquired, including, without limitation those set forth on Exhibit D attached hereto (collectively, the "Mask Works");

(g) Any and all claims for damages by way of past, present and future infringements of any of the rights included above, with the right, but not the obligation, to sue for and collect such damages for said use or infringement of the intellectual property rights identified above;

(h) All licenses or other rights to use any of the Copyrights, Patents, Trademarks, or Mask Works and all license fees and royalties arising from such use to the extent permitted by such license or rights;

(i) All amendments, extensions, renewals and extensions of any of the Copyrights, Trademarks, Patents, or Mask Works; and

(j) All proceeds and products of the foregoing, including without limitation all payments under insurance or any indemnity or warranty payable in respect of any of the foregoing.

Notwithstanding anything to the contrary herein, the Intellectual Property Collateral shall not include any United States intent-to-use trademark or service mark applications filed pursuant to Section 1(b) of the Lanham Act, 15 U.S.C. § 1051, at all times prior to the filing of a "Statement of Use" pursuant to Section 1(d) of the Lanham Act or an "Amendment to Allege Use" pursuant to Section 1(c) of the Lanham Act with respect thereto with the United States Patent and Trademark Office or otherwise.

2. Recordation. Grantor authorizes the Commissioner for Patents, the Commissioner for Trademarks and the Register of Copyrights and any other government officials to record and register this Agreement upon request by Bank.

3. Authorization. Grantor hereby authorizes Bank to (a) modify this Agreement unilaterally by amending the exhibits to this Agreement to include any Intellectual Property Collateral which Grantor obtains subsequent to the date of this Agreement, and (b) file a duplicate original of this Agreement containing amended exhibits reflecting such new Intellectual Property Collateral.

4. Loan Documents. This Agreement has been entered into pursuant to and in conjunction with the Loan Agreement, which is hereby incorporated by reference. The provisions of the Loan Agreement shall supersede and control over any conflicting or inconsistent provision herein. The rights and remedies of Bank with respect to the Intellectual Property Collateral are as provided by the Loan Agreement and related documents, and nothing in this Agreement shall be deemed to limit such rights and remedies.

5. Execution in Counterparts. This Agreement may be executed in counterparts (and by different parties hereto in different counterparts), each of which shall constitute an original, but all of which when taken together shall constitute a single contract. Delivery of an executed counterpart of a signature page to this Agreement by facsimile or in electronic (i.e., "pdf" or "tif" format) shall be effective as delivery of a manually executed counterpart of this Agreement.

6. Successors and Assigns. This Agreement will be binding on and shall inure to the benefit of the parties hereto and their respective successors and assigns.

7. Governing Law. This Agreement and any claim, controversy, dispute or cause of action (whether in contract or tort or otherwise) based upon, arising out of or relating to this Agreement and the transactions contemplated hereby and thereby shall be governed by, and construed in accordance with, the laws of the United States and the Commonwealth of Massachusetts without giving effect to any choice or conflict of law provision or rule (whether of the Commonwealth of Massachusetts or any other jurisdiction).

[Signature page follows.]

IN WITNESS WHEREOF, the parties have caused this Intellectual Property Security Agreement to be duly executed as a sealed instrument under the laws of the Commonwealth of Massachusetts as of the first date written above.

GRANTOR:

NANTERO, INC.

DocuSigned by:
By: Greg Schmergel
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Name: Greg Schmergel

Title: President

BANK:

SILICON VALLEY BANK

DocuSigned by:
By: Joseph Restagno
4A1151AA4EE9439...

Name: Joe Restagno

Title: Managing Director

EXHIBIT A

Copyrights

Description

Registration/
Application
Number

Registration/
Application
Date

None

EXHIBIT B

Patents

<u>Description</u>	<u>Registration/ Application Number</u>	<u>Registration/ Application Date</u>
RESISTIVE CHANGE ELEMENT CELLS SHARING SELECTION DEVICES	US 10825516	27-Feb-2018
LOW POROSITY NANOTUBE ARTICLES	US 10773960	4-Apr-2017
RESISTIVE CHANGE ELEMENT ARRAYS USING A REFERENCE LINE	US 10762961	1-Jul-2019
METHODS OF MAKING SEALED RESISTIVE CHANGE ELEMENTS	US 10741761	14-Jul-2019
LOGIC ELEMENTS COMPRISING CARBON NANOTUBE FIELD EFFECT TRANSISTOR (CNTFET) DEVICES AND METHODS OF MAKING SAME	US 10714537	11-Jun-2018
NON-LINEAR RESISTIVE CHANGE MEMORY CELLS AND ARRAYS	US 10700131	19-Aug-2019
MICROFLUIDIC CONTROL SURFACES USING ORDERED NANOTUBE FABRICS	US 10661304	13-Jul-2017
SCALABLE NANOTUBE FABRICS AND METHODS FOR MAKING SAME	US 10654718	20-Sep-2013
DOUBLE DENSITY NONVOLATILE NANOTUBE SWITCH MEMORY CELLS	US 10546859	8-Oct-2018
METHODS FOR PROGRAMMING 1-R RESISTIVE CHANGE ELEMENT ARRAYS	US 10529422	28-Jan-2019
DEVICES AND METHODS FOR PROGRAMMING RESISTIVE CHANGE ELEMENTS	US 10446228	23-Dec-2017

METHODS FOR FORMING CROSSPOINT ARRAYS OF RESISTIVE CHANGE MEMORY CELLS	US 10403683	23-Mar-2019
METHODS FOR ERROR CORRECTION WITH RESISTIVE CHANGE ELEMENT ARRAYS	US 10387244	13-Jun-2017
SEALED RESISTIVE CHANGE ELEMENTS	US 10355206	12-Apr-2017
RESISTIVE CHANGE ELEMENT ARRAYS WITH IN SITU INITIALIZATION	US 10340005	5-Oct-2017
MEMORY ELEMENTS AND CROSS POINT SWITCHES AND ARRAYS OF SAME USING NONVOLATILE NANOTUBE BLOCKS	US 10339982	29-Jun-2016
DDR COMPATIBLE OPEN ARRAY ARCHITECTURES FOR RESISTIVE CHANGE ELEMENT ARRAYS	US 10290349	14-Aug-2017
DEVICES AND METHODS FOR ACCESSING RESISTIVE CHANGE ELEMENTS IN RESISTIVE CHANGE ELEMENT ARRAYS	US 10290327	13-Oct-2017
METHODS FOR ERROR CORRECTION WITH RESISTIVE CHANGE ELEMENT ARRAYS	US 10261861	13-Jun-2017
RESISTIVE CHANGE ELEMENTS INCORPORATING CARBON BASED DIODE SELECT DEVICES	US 10249684	5-Mar-2018
NONVOLATILE NANOTUBE SWITCHES AND SYSTEMS USING SAME	US 10204682	18-Sep-2017
METHODS FOR PROGRAMMING 1-R RESISTIVE CHANGE ELEMENT ARRAYS	US 10192619	24-Jul-2017
TWO-TERMINAL SWITCHING DEVICES COMPRISING COATED NANOTUBE ELEMENTS	US 10181569	1-Sep-2017

METHODS FOR ARRANGING NANOSCOPIC ELEMENTS WITHIN NETWORKS, FABRICS AND FILMS	US 10124367	19-Aug-2016
STACKED THREE-DIMENSIONAL ARRAYS OF TWO TERMINAL NANOTUBE SWITCHING DEVICES	US 10096601	30-Jan-2018
METHODS OF FORMING NANOTUBE FILMS AND ARTICLES	US 10096363	25-Jan-2016
METHODS FOR FORMING NANOTUBE FABRIC LAYERS WITH INCREASED DENSITY	US 10084138	21-Nov-2016
NANOTUBE SOLUTIONS WITH HIGH CONCENTRATION AND LOW CONTAMINATION AND METHODS FOR PURIFYING NANOTUBE SOLUTIONS	US 10069072	31-May-2013
LOGIC ELEMENTS COMPRISING CARBON NANOTUBE FIELD EFFECT TRANSISTOR (CNTFET) DEVICES AND METHODS OF MAKING SAME	US 10002908	20-May-2016
METHODS FOR ENHANCED STATE RETENTION WITHIN A RESISTIVE CHANGE CELL	US 9947400	22-Apr-2016
CIRCUITS FOR DETERMINING THE RESISTIVE STATES OF RESISTIVE CHANGE ELEMENTS	US 9941001	7-Jun-2016
METHODS FOR DETERMINING THE RESISTIVE STATES OF RESISTIVE CHANGE ELEMENTS	US 9934848	7-Jun-2016
RESISTIVE CHANGE ELEMENT ARRAY USING VERTICALLY ORIENTED BIT LINES	US 9917139	20-Dec-2016
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	US 9911743	8-Aug-2007

METHODS FOR PROGRAMMING AND ACCESSING DDR COMPATIBLE RESISTIVE CHANGE ELEMENT ARRAYS	US 9852793	23-Jun-2016
CROSS POINT ARRAYS OF 1-R NONVOLATILE RESISTIVE CHANGE MEMORY CELLS USING CONTINUOUS NANOTUBE FABRICS	US 9783255	29-Jun-2016
NON-VOLATILE COMPOSITE NANOSCOPIC FABRIC NAND MEMORY ARRAYS AND METHODS OF MAKING SAME	US 9767902	14-Mar-2016
RESISTIVE MATERIALS COMPRISING MIXED NANOSCOPIC PARTICLES AND CARBON NANOTUBES	US 9755170	11-Apr-2016
1-R RESISTIVE CHANGE ELEMENT ARRAYS USING RESISTIVE REFERENCE ELEMENTS	US 9715927	24-Mar-2016
RESISTIVE CHANGE ELEMENT ARRAYS USING RESISTIVE REFERENCE ELEMENTS	US 9666272	12-Jan-2016
LOW DEFECT NANOTUBE APPLICATION SOLUTIONS AND FABRICS AND METHODS OF MAKING SAME	US 9650732	30-Apr-2014
NANOTUBE SOLUTION TREATED WITH MOLECULAR ADDITIVE NANOTUBE FILM HAVING ENHANCED ADHESION PROPERTY AND METHODS FOR FORMING THE NANOTUBE SOLUTION AND THE NANOTUBE FILM	US 9634251	9-Mar-2012
METHODS FOR CONTROLLING DENSITY POROSITY AND/OR GAP SIZE WITHIN NANOTUBE FABRIC LAYERS AND FILMS	US 9617151	31-Oct-2012

REVERSIBLE NANOSWITCH	US 9601498	23-May-2011
METHODS FOR ARRANGING NANOTUBE ELEMENTS WITHIN NANOTUBE FABRICS AND FILMS	US 9574290	12-Nov-2010
METHODS FOR PASSIVATING A CARBONIC NANOLAYER	US 9502675	4-Mar-2016
METHODS FOR ARRANGING NANOSCOPIC ELEMENTS WITHIN NETWORKS FABRICS AND FILMS	US 9422651	30-Mar-2011
DDR COMPATIBLE MEMORY CIRCUIT ARCHITECTURE FOR RESISTIVE CHANGE ELEMENT ARRAYS	US 9412447	29-Jul-2015
MEMORY ELEMENTS AND CROSS POINT SWITCHES AND ARRAYS OF SAME USING NONVOLATILE NANOTUBE BLOCKS	US 9406349	2-May-2014
CARBON BASED NONVOLATILE CROSS POINT MEMORY INCORPORATING CARBON BASED DIODE SELECT DEVICES AND MOSFET SELECT DEVICES FOR MEMORY AND LOGIC APPLICATIONS	US 9390790	17-Dec-2012
LOGIC ELEMENTS COMPRISING CARBON NANOTUBE FIELD EFFECT TRANSISTOR (CNTFET) DEVICES AND METHODS OF MAKING SAME	US 9362390	28-Mar-2013
AN IMPROVED TWO-TERMINAL SWITCHING DEVICE USING A COMPOSITE MATERIAL OF NANOSCOPIC PARTICLES AND CARBON NANOTUBES	US 9337423	27-Feb-2015
METHODS FOR READING AND PROGRAMMING 1-R RESISTIVE CHANGE ELEMENT ARRAYS	US 9299430	22-Jan-2015

NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	US 9287356	20-Jan-2009
METHODS FOR PASSIVATING A CARBONIC NANOLAYER	US 9281185	7-Nov-2014
METHOD FOR DYNAMICALLY ACCESSING AND PROGRAMMING RESISTIVE CHANGE ELEMENT ARRAYS	US 9263126	12-Aug-2014
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	US 9196615	8-Aug-2007
ELECTROSTATIC DISCHARGE PROTECTION CIRCUITS USING CARBON NANOTUBE FIELD EFFECT TRANSISTOR (CNTFET) DEVICES AND METHODS OF MAKING SAME	US 9007732	15-Mar-2013
SWITCHING MATERIALS COMPRISING MIXED NANOSCOPIC PARTICLES AND CARBON NANOTUBES AND METHOD OF MAKING AND USING SAME	US 8969142	11-Oct-2013
METHODS FOR ADJUSTING THE CONDUCTIVITY RANGE OF A NANOTUBE FABRIC LAYER	US 8941094	2-Sep-2010
MICROSTRIP ANTENNA ELEMENTS AND ARRAYS COMPRISING A SHAPED NANOTUBE FABRIC LAYER AND INTEGRATED TWO TERMINAL NANOTUBE SELECT DEVICES	US 8937575	31-Jul-2009

METHODS FOR PASSIVATING A CARBONIC NANOLAYER	US 8895950	6-Sep-2013
MEMORY ELEMENTS AND CROSS POINT SWITCHES AND ARRAYS OF SAME USING NONVOLATILE NANOTUBE BLOCKS	US 8809917	29-Jul-2009
AQUEOUS CARBON NANOTUBE APPLICATOR LIQUIDS AND METHODS FOR PRODUCING APPLICATOR LIQUIDS THEREOF	US 8771628	4-Nov-2009
FIELD EFFECT DEVICES HAVING A DRAIN CONTROLLED VIA A NANOTUBE SWITCHING ELEMENT	US 8699268	5-Oct-2007
CARBON NANOTUBE-BASED NEURAL NETWORKS AND METHODS OF MAKING AND USING SAME	US 8659940	24-Mar-2011
METHODS OF MAKING NANOTUBE SWITCHES	US 8631562	23-Nov-2010
CARBON NANOTUBES FOR THE SELECTIVE TRANSFER OF HEAT FROM ELECTRONICS	US 8630091	19-Apr-2011
SPIN-COATABLE LIQUID FOR FORMATION OF HIGH PURITY NANOTUBE FILMS	US 8628692	25-May-2012
A METHOD FOR ADJUSTING A RESISTIVE CHANGE ELEMENT USING A REFERENCE	US 8619450	1-Sep-2010
NRAM ARRAYS WITH NANOTUBE BLOCKS NANOTUBE TRACES AND NANOTUBE PLANES AND METHODS OF MAKING SAME	US 8587989	17-Jun-2009

SWITCHING MATERIALS COMPRISING MIXED NANOSCOPIC PARTICLES AND CARBON NANOTUBES AND METHOD OF MAKING AND USING SAME	US 8586424	29-Mar-2011
MEMORY ARRAYS USING NANOTUBE ARTICLES WITH REPROGRAMMABLE RESISTANCE	US 8580586	15-Jan-2009
ANISOTROPIC NANOTUBE FABRIC LAYERS AND FILMS AND METHODS OF FORMING SAME	US 8574673	31-Jul-2009
PRODUCTION OF CARBON NANOTUBES	US 8562937	2-Oct-2008
METHODS FOR PASSIVATING A CARBONIC NANOLAYER	US 8551806	22-Oct-2010
NONVOLATILE NANOTUBE PROGRAMMABLE LOGIC DEVICES AND A NONVOLATILE NANOTUBE FIELD PROGRAMMABLE GATE ARRAY USING SAME	US 8541843	6-Aug-2009
METHOD AND SYSTEM OF USING NANOTUBE FABRICS AS JOULE HEATING ELEMENTS FOR MEMORIES AND OTHER APPLICATIONS	US 8525143	9-Dec-2008
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	US 8513768	8-Aug-2007
LIGHT EMITTERS USING NANOTUBES AND METHODS OF MAKING SAME	US 8471238	15-Sep-2005
CARBON NANOTUBE FILMS LAYERS FABRICS RIBBONS ELEMENTS AND ARTICLES	US 8400053	10-Jun-2008

NANOTUBE FABRIC-BASED SENSOR SYSTEMS AND METHODS OF MAKING SAME	US 8366999	23-Sep-2008
FIELD EFFECT DEVICE HAVING A CHANNEL OF NANOFABRIC AND METHOD OF MAKING SAME	US 8362525	13-Jan-2006
INTEGRATED THREE-DIMENSIONAL SEMICONDUCTOR SYSTEM COMPRISING NONVOLATILE NANOTUBE FIELD EFFECT TRANSISTORS	US 8357921	6-Aug-2009
SENSOR PLATFORM USING A NON-HORIZONTALLY ORIENTED NANOTUBE ELEMENT	US 8357559	20-May-2009
DYNAMIC SENSE CURRENT SUPPLY CIRCUIT AND ASSOCIATED METHOD FOR READING AND CHARACTERIZING A RESISTIVE MEMORY ARRAY	US 8351239	23-Oct-2009
METHOD OF ALIGNING NANOTUBES AND WIRES WITH AN ETCHED FEATURE	US 8343373	13-Aug-2009
NONVOLATILE NANOTUBE PROGRAMMABLE LOGIC DEVICES AND A NONVOLATILE NANOTUBE FIELD PROGRAMMABLE GATE ARRAY USING SAME	US 8319205	6-Aug-2009
SENSOR PLATFORM USING A HORIZONTALLY ORIENTED NANOTUBE ELEMENT	US 8310015	17-Jan-2006
COMPACT ELECTRICAL SWITCHING DEVICES WITH NANOTUBES ELEMENTS AND METHODS OF MAKING SAME	US 8222704	31-Dec-2009

NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	US 8217490	8-Aug-2007
NONVOLATILE NANOTUBE PROGRAMMABLE LOGIC DEVICES AND A NONVOLATILE NANOTUBE FIELD PROGRAMMABLE GATE ARRAY USING SAME	US 8188763	6-Aug-2009
SPIN-COATABLE LIQUID FOR FORMATION OF HIGH PURITY NANOTUBE FILMS	US 8187502	25-Jul-2007
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	US 8183665	19-Nov-2008
SPIN-COATABLE LIQUID FOR FORMATION OF HIGH PURITY NANOTUBE FILMS	US 8147722	25-Jul-2007
TWO-TERMINAL NANOTUBE DEVICES INCLUDING A NANOTUBE BRIDGE AND METHODS OF MAKING SAME	US 8134220	16-Jun-2008
ANISOTROPIC NANOTUBE FABRIC LAYERS AND FILMS AND METHODS OF FORMING SAME	US 8128993	31-Jul-2009
ELECTROMAGNETIC AND THERMAL SENSORS USING CARBON NANOTUBES AND METHODS OF MAKING SAME	US 8110883	12-Mar-2008
NONVOLATILE RESISTIVE MEMORIES HAVING SCALABLE TWO-TERMINAL NANOTUBE SWITCHES	US 8102018	8-Aug-2007

DEVICE SELECTION CIRCUITRY CONSTRUCTED WITH NANOTUBE TECHNOLOGY	US 8101976	11-Sep-2007
METHOD OF FORMING A CARBON NANO-TUBE BASED CONTACT TO SEMICONDUCTOR	US 8044388	21-Jul-2009
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	US 8013363	8-Aug-2007
LATCH CIRCUITS AND OPERATION CIRCUITS HAVING SCALABLE NONVOLATILE NANOTUBE SWITCHES AS ELECTRONIC FUSE REPLACEMENT ELEMENTS	US 8008745	8-Aug-2007
METHOD FOR RESETTNG A RESISTIVE CHANGE MEMORY ELEMENT	US 8000127	13-Nov-2009
NON-VOLATILE SHADOW LATCH USING A NANOTUBE SWITCH	US 7986546	30-Jun-2008
NANOTUBE-BASED SWITCHING ELEMENTS AND LOGIC CIRCUITS	US 7985906	22-Nov-2010
CARBON NANOTUBE RESONATORS	US 7965156	3-Sep-2008
METHOD OF FABRICATING A PATTERNED NANOSCOPIC ARTICLE	US 7948082	21-Aug-2008
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	US 7948054	23-Aug-2010
RANDOM ACCESS MEMORY INCLUDING NANOTUBE SWITCHING ELEMENTS	US 7944735	31-Aug-2009

NON-VOLATILE ELECTROMECHANICAL FIELD EFFECT DEVICES AND CIRCUITS USING SAME AND METHODS OF FORMING SAME	US 7943464	4-Sep-2009
NON-VOLATILE ELECTROMECHANICAL FIELD EFFECT DEVICES AND CIRCUITS USING SAME AND METHODS OF FORMING SAME	US 7928523	30-Jul-2009
NON-TENSIONED CARBON NANOTUBE SWITCH DESIGN AND PROCESS FOR MAKING SAME	US 7928521	31-May-2005
CARBON NANOTUBES FOR THE SELECTIVE TRANSFER OF HEAT FROM ELECTRONICS	US 7927992	6-Mar-2008
SWITCHING MATERIALS COMPRISING MIXED NANOSCOPIC PARTICLES AND CARBON NANOTUBES AND METHOD OF MAKING AND USING SAME	US 7915637	19-Nov-2008
METHODS OF MAKING ELECTROMECHANICAL THREE-TRACE JUNCTION DEVICES	US 7915066	2-Sep-2008
NANOTUBE-ON-GATE FET STRUCTURES AND APPLICATIONS	US 7911831	13-Nov-2007
RESISTIVE ELEMENTS USING CARBON NANOTUBES	US 7859385	29-Apr-2008
INTEGRATED NANOTUBE AND FIELD EFFECT SWITCHING DEVICES	US 7859311	21-Jul-2009
METHOD OF ALIGNING DEPOSITED NANOTUBES ONTO AN ETCHED FEATURE USING A SPACER	US 7858979	29-May-2009
HIGH PURITY NANOTUBE FABRICS AND FILMS	US 7858185	3-Jun-2004

HYBRID CARBON NANOTUBE FET(CNFET)-FET STATIC RAM (SRAM) AND METHOD OF MAKING SAME	US 7855403	29-Sep-2009
NONVOLATILE NANOTUBE PROGRAMMABLE LOGIC DEVICES AND A NONVOLATILE NANOTUBE FIELD PROGRAMMABLE GATE ARRAY USING SAME	US 7852114	6-Aug-2009
NONVOLATILE NANOTUBE PROGRAMMABLE LOGIC DEVICES AND A NONVOLATILE NANOTUBE FIELD PROGRAMMABLE GATE ARRAY USING SAME	US 7847588	6-Aug-2009
NANOTUBE ESD PROTECTIVE DEVICES AND CORRESPONDING NONVOLATILE AND VOLATILE NANOTUBE SWITCHES	US 7839615	27-Jul-2009
METHODS OF MAKING NANOTUBE-BASED SWITCHING ELEMENTS AND LOGIC CIRCUITS	US 7839176	2-Jun-2009
MEMORY ELEMENTS AND CROSS POINT SWITCHES AND ARRAYS OF SAME USING NONVOLATILE NANOTUBE BLOCKS	US 7835170	8-Aug-2007
HYBRID CIRCUIT HAVING NANOTUBE MEMORY CELLS	US 7817458	13-Feb-2008
SENSOR PLATFORM USING A NON- HORIZONTALLY ORIENTED NANOTUBE ELEMENT	US 7786540	11-Jul-2007
VOLATILE NANOTUBE-BASED SWITCHING ELEMENTS WITH MULTIPLE CONTROLS	US 7782652	6-Oct-2008

NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	US 7782650	8-Aug-2007
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	US 7781862	15-Nov-2005
SENSOR PLATFORM USING A HORIZONTALLY ORIENTED NANOTUBE ELEMENT	US 7780918	12-May-2004
NANOTUBE DEVICE STRUCTURE AND METHODS OF FABRICATION	US 7777222	26-Aug-2009
TRI-STATE CIRCUIT USING NANOTUBE SWITCHING ELEMENTS	US 7768304	30-Oct-2007
STORAGE ELEMENTS USING NANOTUBE SWITCHING ELEMENTS	US 7759996	26-Jun-2008
NANOTUBE FILMS AND ARTICLES	US 7745810	9-Feb-2004
RECEIVER CIRCUIT USING NANOTUBE-BASED SWITCHES AND TRANSISTORS	US 7737471	11-Feb-2008
RECEIVER CIRCUIT USING NANOTUBE-BASED SWITCHES AND LOGIC	US 7720514	12-Feb-2008
DEVICES HAVING VERTICALLY-DISPOSED NANOFABRIC ARTICLES AND METHODS OF MAKING THE SAME	US 7719067	25-Sep-2006
NANOTUBE-BASED SWITCHING ELEMENTS WITH MULTIPLE CONTROLS AND LOGIC CIRCUITS HAVING SAID ELEMENTS	US 7710157	6-Oct-2008
FIELD EFFECT DEVICES HAVING A GATE CONTROLLED VIA A NANOTUBE SWITCHING ELEMENT	US 7709880	30-Apr-2007

AQUEOUS CARBON NANOTUBE APPLICATOR LIQUIDS AND METHODS FOR PRODUCING APPLICATOR LIQUIDS THEREOF	US 7666382	15-Dec-2005
ISOLATION STRUCTURE FOR DEFLECTABLE NANOTUBE ELEMENTS	US 7663911	30-Oct-2007
APPLICATOR LIQUID CONTAINING ETHYL LACTATE FOR PREPARATION OF NANOTUBE FILMS	US 7658869	3-Jun-2004
NANOTUBE-BASED SWITCHING ELEMENTS	US 7652337	3-Oct-2006
CIRCUIT ARRAYS HAVING CELLS WITH COMBINATIONS OF TRANSISTORS AND NANOTUBE SWITCHING ELEMENTS	US 7649769	27-Nov-2007
DEVICES HAVING HORIZONTALLY-DISPOSED NANOFABRIC ARTICLES AND METHODS OF MAKING THE SAME	US 7619291	4-Dec-2007
HYBRID CARBON NANOTUBE FET(CNFET)-FET STATIC RAM (SRAM) AND METHOD OF MAKING SAME	US 7598544	13-Jan-2006
NANOTUBE FUSE STRUCTURE	US 7598127	22-Nov-2005
NON-VOLATILE ELECTROMECHANICAL FIELD EFFECT DEVICES AND CIRCUITS USING SAME AND METHODS OF FORMING SAME	US 7595527	25-Sep-2007
NANOTUBE DEVICE STRUCTURE AND METHODS OF FABRICATION	US 7588960	9-Jun-2006
RANDOM ACCESS MEMORY INCLUDING NANOTUBE SWITCHING ELEMENTS	US 7583526	17-Jul-2007

METHOD OF ALIGNING NANOTUBES AND WIRES WITH AN ETCHED FEATURE	US 7575693	14-Dec-2005
NON-VOLATILE ELECTROMECHANICAL FIELD EFFECT DEVICES AND CIRCUITS USING SAME AND METHODS OF FORMING SAME	US 7569880	2-Apr-2007
NANOTUBE ESD PROTECTIVE DEVICES AND CORRESPONDING NONVOLATILE AND VOLATILE NANOTUBE SWITCHES	US 7567414	2-Nov-2005
METHODS OF MAKING CARBON NANOTUBE FILMS LAYERS FABRICS RIBBONS ELEMENTS AND ARTICLES	US 7566478	13-Jan-2003
INTEGRATED NANOTUBE AND FIELD EFFECT SWITCHING DEVICES	US 7564269	30-Oct-2007
METHOD OF FORMING A CARBON NANOTUBE-BASED CONTACT TO SEMICONDUCTOR	US 7563711	21-Feb-2007
METHODS OF USING THIN METAL LAYERS TO MAKE CARBON NANOTUBE FILMS LAYERS FABRICS RIBBONS ELEMENTS AND ARTICLES	US 7560136	13-Jan-2003
METHOD OF MAKING AN APPLICATOR LIQUID FOR ELECTRONICS FABRICATION PROCESS	US 7556746	3-Jun-2004
NANOTUBE-BASED SWITCHING ELEMENTS WITH MULTIPLE CONTROLS	US 7542334	9-Jan-2008
NANOTUBE-BASED SWITCHING ELEMENTS AND LOGIC CIRCUITS	US 7541842	21-Nov-2006

METHOD OF ALIGNING DEPOSITED NANOTUBES ONTO AN ETCHED FEATURE USING A SPACER	US 7541216	14-Dec-2005
SENSOR PLATFORM USING A NON-HORIZONTALLY ORIENTED NANOTUBE ELEMENT	US 7538400	17-Jan-2006
ELECTROMECHANICAL MEMORY ARRAY USING NANOTUBE RIBBONS AND METHOD FOR MAKING SAME	US 7511318	19-Nov-2007
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	US 7504051	3-Jun-2004
MEMORY ARRAYS USING NANOTUBE ARTICLES WITH REPROGRAMMABLE RESISTANCE	US 7479654	15-Nov-2005
METHODS OF MAKING ELECTROMECHANICAL THREE-TRACE JUNCTION DEVICES	US 7419845	25-Jul-2005
PATTERNED NANOSCOPIC ARTICLES ON A SUBSTRATE AND METHODS OF MAKING THE SAME	US 7416993	8-Sep-2004
STORAGE ELEMENTS USING NANOTUBE SWITCHING ELEMENTS	US 7405605	9-Jan-2007
NANO STRUCTURE ELECTRODE DESIGN	US 7402770	9-Nov-2005
NON-VOLATILE SHADOW LATCH USING A NANOTUBE SWITCH	US 7394687	15-Nov-2005
SENSOR PLATFORM USING A NON-HORIZONTALLY ORIENTED NANOTUBE ELEMENT	US 7385266	12-May-2004
SPIN-COATABLE LIQUID FOR FORMATION OF HIGH PURITY NANOTUBE FILMS	US 7375369	3-Jun-2004
RESISTIVE ELEMENTS USING CARBON NANOTUBES	US 7365632	20-Sep-2005

HYBRID CIRCUIT HAVING NANOTUBE ELECTROMECHANICAL MEMORY	US 7342818	13-Oct-2004
NANOTUBE-BASED SWITCHING ELEMENTS WITH MULTIPLE CONTROLS	US 7339401	4-Aug-2005
METHODS OF NANOTUBE FILMS AND ARTICLES	US 7335528	8-Dec-2004
METHODS OF USING PRE-FORMED NANOTUBES TO MAKE CARBON NANOTUBE FILMS LAYERS FABRICS RIBBONS ELEMENTS AND ARTICLES	US 7335395	13-Jan-2003
RECEIVER CIRCUIT USING NANOTUBE-BASED SWITCHES AND LOGIC	US 7330709	10-Jan-2005
RECEIVER CIRCUIT USING NANOTUBE-BASED SWITCHES AND TRANSISTORS	US 7329931	10-Jan-2005
DEVICES HAVING HORIZONTALLY-DISPOSED NANOFABRIC ARTICLES AND METHODS OF MAKING THE SAME	US 7304357	29-Jul-2005
CIRCUIT ARRAYS HAVING CELLS WITH COMBINATIONS OF TRANSISTORS AND NANOTUBE SWITCHING ELEMENTS	US 7301802	9-Jun-2004
ISOLATION STRUCTURE FOR DEFLECTABLE NANOTUBE ELEMENTS	US 7289357	13-Aug-2004
INTEGRATED NANOTUBE AND FIELD EFFECT SWITCHING DEVICE	US 7288970	10-Jan-2005
DEVICES HAVING VERTICALLY-DISPOSED NANOFABRIC ARTICLES AND METHODS OF MAKING THE SAME	US 7274078	22-Jun-2005

NON-VOLATILE ELECTROMECHANICAL FIELD EFFECT DEVICES AND CIRCUITS USING SAME AND METHODS OF FORMING SAME	US 7274064	18-Oct-2004
DEVICE SELECTION CIRCUITRY CONSTRUCTED WITH NANOTUBE TECHNOLOGY	US 7269052	10-Oct-2006
NON-VOLATILE ELECTROMECHANICAL FIELD EFFECT DEVICES AND CIRCUITS USING SAME AND METHODS OF FORMING SAME	US 7268044	2-Oct-2006
NANOTUBE-BASED LOGIC DRIVER CIRCUITS	US 7265575	16-Jan-2007
METHODS OF NANOTUBE FILMS AND ARTICLES	US 7264990	13-Dec-2004
DEVICES HAVING HORIZONTALLY-DISPOSED NANOFABRIC ARTICLES AND METHODS OF MAKING THE SAME	US 7259410	11-Feb-2004
RANDOM ACCESS MEMORY INCLUDING NANOTUBE SWITCHING ELEMENTS	US 7245520	20-Sep-2005
FIELD EFFECT DEVICES HAVING A GATE CONTROLLED VIA A NANOTUBE SWITCHING ELEMENT	US 7211854	9-Jun-2004
NANOTUBE-BASED SWITCHING ELEMENTS AND LOGIC CIRCUITS	US 7138832	13-Aug-2004
DEVICE SELECTION CIRCUITRY CONSTRUCTED WITH NANOTUBE TECHNOLOGY	US 7120047	24-Oct-2003
NANOTUBE-BASED SWITCHING ELEMENTS	US 7115960	13-Aug-2004

NON-VOLATILE ELECTROMECHANICAL FIELD EFFECT DEVICES AND CIRCUITS USING SAME AND METHODS OF FORMING SAME	US 7115901	9-Jun-2004
NON-VOLATILE RAM CELL AND ARRAY USING NANOTUBE SWITCH POSITION FOR INFORMATION STATE	US 7113426	26-Mar-2004
METHOD OF MAKING NON-VOLATILE FIELD EFFECT DEVICES AND ARRAYS OF SAME	US 7112493	9-Jun-2004
DEVICES HAVING VERTICALLY-DISPOSED NANOFABRIC ARTICLES AND METHODS OF MAKING THE SAME	US 7112464	21-Jun-2005
FOUR TERMINAL NON-VOLATILE TRANSISTOR DEVICE	US 7075141	26-Mar-2004
NANOTUBE DEVICE STRUCTURE AND METHODS OF FABRICATION	US 7071023	13-Aug-2004
PROCESS FOR MAKING BIT SELECTABLE DEVICES HAVING ELEMENTS MADE WITH NANOTUBES	US 7045421	15-Apr-2004
FIELD EFFECT DEVICES HAVING A SOURCE CONTROLLED VIA A NANOTUBE SWITCHING ELEMENT	US 6982903	9-Jun-2004
METHODS OF MAKING ELECTROMECHANICAL THREE-TRACE JUNCTION DEVICES	US 6979590	15-Apr-2004
NANOTUBE FILMS AND ARTICLES	US 6942921	11-Feb-2004
ELECTROMECHANICAL MEMORY ARRAY USING NANOTUBE RIBBONS AND METHOD FOR MAKING SAME	US 6919592	25-Jul-2001
ELECTROMECHANICAL THREE-TRACE JUNCTION DEVICES	US 6911682	28-Dec-2001

HYBRID CIRCUIT HAVING NANOTUBE ELECTROMECHANICAL MEMORY	US 6836424	5-Mar-2003
METHODS OF NANOTUBE FILMS AND ARTICLES	US 6835591	23-Apr-2002
METHODS OF MAKING ELECTROMECHANICAL THREE-TRACE JUNCTION DEVICES	US 6784028	28-Dec-2001
NANOTUBE FILMS AND ARTICLES	US 6706402	23-Apr-2002
ELECTROMECHANICAL MEMORY HAVING CELL SELECTION CIRCUITRY CONSTRUCTED WITH NANOTUBE TECHNOLOGY	US 6643165	25-Jul-2001
HYBRID CIRCUIT HAVING NANOTUBE ELECTROMECHANICAL MEMORY	US 6574130	25-Jul-2001
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	UK 2057633	8-Aug-2007
NANOTUBE FABRIC-BASED SENSOR SYSTEM AND METHODS OF MAKING SAME	UK 1929276	6-Sep-2006
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	UK 1880420	9-May-2006
AQUEOUS CARBON NANOTUBE APPLICATOR LIQUIDS AND METHOD FOR PRODUCING APPLICATOR LIQUIDS THEREOF	UK 1825038	15-Dec-2005
INTEGRATED NANOTUBE AND FIELD EFFECT SWITCHING DEVICE	UK 1776763	26-May-2005
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	UK 1751778	26-May-2005

METHODS OF NANOTUBE FILMS AND ARTICLES	UK 1409156	25-Jul-2002
DDR COMPATIBLE MEMORY CIRCUIT ARCHITECTURE FOR RESISTIVE CHANGE ELEMENT ARRAYS	TW I684179	29-Jul-2015
METHODS FOR READING AND PROGRAMMING 1-R RESISTIVE CHANGE ELEMENT ARRAYS	TW I653629	20-Jan-2016
NRAM ARRAYS WITH NANOTUBE BLOCKS, NANOTUBE TRACES, AND NANOTUBE PLANES AND METHODS OF MAKING SAME	TW I588986	19-Jun-2009
NONVOLATILE NANOTUBE PROGRAMMABLE LOGIC DEVICES AND A NONVOLATILE NANOTUBE FIELD PROGRAMMABLE GATE ARRAY USING SAME	TW I552154	13-Aug-2009
ANISOTROPIC NANOTUBE FABRIC LAYERS AND FILMS AND METHODS OF FORMING SAME	TW I544520	30-Jul-2010
NONVOLATILE NANOTUBE PROGRAMMABLE LOGIC DEVICES AND A NONVOLATILE NANOTUBE FIELD PROGRAMMABLE GATE ARRAY USING SAME	TW I543363	13-Aug-2009
METHODS FOR PASSIVATING A CARBONIC NANOLAYER	TW I527753	25-Oct-2010
CARBON NANOTUBE-BASED NEURAL NETWORKS AND METHODS OF MAKING AND USING SAME	TW I502522	25-Mar-2009
NANOTUBE ESD PROTECTIVE DEVICES AND CORRESPONDING NONVOLATILE AND VOLATILE NANOTUBE SWITCHES	TW I488206	10-Aug-2009

ELECTROMAGNETIC AND THERMAL SENSORS USING CARBON NANOTUBES AND METHODS OF MAKING SAME	TW I475673	20-Mar-2008
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	TW I463673	8-Aug-2007
TRIODES USING NANOFABRIC ARTICLES AND METHODS OF MAKING THE SAME	TW I461350	21-May-2008
TWO-TERMINAL NANOTUBE DEVICES INCLUDING A NANOTUBE BRIDGE AND METHODS OF MAKING SAME	TW I435446	20-Jun-2008
METHOD OF FORMING A CARBON NANO-TUBE BASED CONTACT TO SEMICONDUCTOR	TW I421918	21-Feb-2008
MEMORY ELEMENTS AND CROSS POINT SWITCHES AND ARRAYS OF SAME USING NONVOLATILE NANOTUBE BLOCKS	TW I419163	8-Aug-2007
AQUEOUS CARBON NANOTUBE APPLICATOR LIQUIDS AND METHODS FOR PRODUCING APPLICATOR LIQUIDS THEREOF	TW I417411	16-Dec-2005
RANDOM ACCESS MEMORY INCLUDING NANOTUBE SWITCHING ELEMENTS	TW I410969	21-Sep-2005
LIGHT EMITTERS USING NANOTUBES AND METHODS OF MAKING SAME	TW I399864	15-Sep-2005
RESISTIVE ELEMENTS USING CARBON NANOTUBES	TW I348169	20-Sep-2005
SENSOR PLATFORM USING A NON-HORIZONTALLY ORIENTED NANOTUBE ELEMENT	TW I346202	14-May-2004

NANOTUBE-BASED SWITCHING ELEMENTS	TW I343182	13-Aug-2004
SENSOR PLATFORM USING A HORIZONTALLY ORIENTED NANOTUBE ELEMENT	TW I330403	14-May-2004
REVERSIBLE NANOSWITCH	TW I329348	8-May-2006
MEMORY ARRAYS USING NANOTUBE ARTICLES WITH REPROGRAMMABLE RESISTANCE	TW I328227	8-May-2006
METHODS OF NANOTUBE FILMS AND ARTICLES	TW I324786	10-Jan-2003
NON-VOLATILE SHADOW LATCH USING A NANOTUBE SWITCH	TW I324773	8-May-2006
DEVICES HAVING HORIZONTALLY-DISPOSED NANOFABRIC ARTICLES AND METHODS OF MAKING THE SAME	TW I323479	11-Feb-2004
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	TW I317952	2-Jun-2005
CARBON NANOTUBE FILMS LAYERS FABRICS RIBBONS ELEMENTS AND ARTICLES	TW I313669	24-Jan-2003
NANOTUBE-BASED TRANSFER DEVICES AND RELATED CIRCUITS	TW I305049	17-Jun-2005
ELECTROMECHANICAL THREE-TRACE JUNCTION DEVICES	TW I303421	27-Dec-2002
HIGH PURITY NANOTUBE FABRICS AND FILMS	TW I300046	2-Jun-2005
NANOTUBE FILMS AND ARTICLES	TW I298709	10-Jan-2003
SPIN-COATABLE LIQUID FOR FORMATION OF HIGH PURITY NANOTUBE FILMS	TW I289147	2-Jun-2005
METHODS OF USING PRE-FORMED NANOTUBES TO MAKE CARBON NANOTUBE FILMS LAYERS FABRICS RIBBONS ELEMENTS AND ARTICLES	TW I269348	24-Jan-2003

METHODS OF USING THIN METAL LAYERS TO MAKE CARBON NANOTUBE FILMS LAYERS FABRICS RIBBONS ELEMENTS AND ARTICLES	TW I268961	24-Jan-2003
ELECTROMECHANICAL MEMORY ARRAY USING NANOTUBE RIBBONS AND METHOD FOR MAKING SAME	TW I246788	10-Jan-2003
NANOTUBE-BASED SWITCHING ELEMENTS WITH MULTIPLE CONTROLS	TW 355073	13-Aug-2004
MEMORY ARRAYS USING NANOTUBE ARTICLES WITH REPROGRAMMABLE RESISTANCE	SN 137294	9-May-2006
NON-VOLATILE SHADOW LATCH USING A NANOTUBE SWITCH	SN 137293	9-May-2006
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	SN 137291	9-May-2006
NANOTUBE FILMS AND ARTICLES	SN 101867	25-Jul-2002
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	NL 2057633	8-Aug-2007
AQUEOUS CARBON NANOTUBE APPLICATOR LIQUIDS AND METHOD FOR PRODUCING APPLICATOR LIQUIDS THEREOF	NL 1825038	15-Dec-2005
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	NL 1751778	26-May-2005
METHODS FOR READING AND PROGRAMMING 1-R RESISTIVE CHANGE ELEMENT ARRAYS	KR 10-2038738	20-Jan-2016

METHODS FOR ARRANGING NANOSCOPIC ELEMENTS WITHIN NETWORKS, FABRICS, AND FILMS	KR 1938425	24-Oct-2012
METHODS FOR CONTROLLING DENSITY POROSITY AND/OR GAP SIZE WITHIN NANOTUBE FABRIC LAYERS AND FILMS	KR 1709823	14-Feb-2011
NONVOLATILE RESISTIVE MEMORIES LATCH CIRCUITS AND OPERATION CIRCUITS HAVING SCALABLE TWO-TERMINAL NANOTUBE SWITCHES	KR 1486406	8-Aug-2007
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	KR 1461688	8-Aug-2007
NON-VOLATILE SHADOW LATCH USING A NANOTUBE SWITCH	KR 1280105	9-May-2006
MEMORY ELEMENTS AND CROSS POINT SWITCHES AND ARRAYS OF SAME USING NONVOLATILE NANOTUBE BLOCKS	KR 1169499	8-Aug-2007
NANOTUBE FILMS AND ARTICLES	KR 899587	25-Jul-2002
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	KR 880280	26-May-2005
DDR COMPATIBLE MEMORY CIRCUIT ARCHITECTURE FOR RESISTIVE CHANGE ELEMENT ARRAYS	JP 6559099	29-Jul-2015
METHOD FOR DYNAMICALLY ACCESSING AND PROGRAMMING RESISTANCE CHANGE ELEMENT ARRAY	JP 6523431	10-Aug-2015

METHOD FOR READING AND PROGRAMMING 1-R RESISTANCE CHANGE ELEMENT ARRAY	JP 6412515	21-Jan-2016
METHODS FOR ARRANGING NANOSCOPIC ELEMENTS WITHIN NETWORKS FABRICS AND FILMS	JP 6130787	30-Mar-2011
MEMORY ELEMENTS AND CROSS POINT SWITCHES AND ARRAYS OF SAME USING NONVOLATILE NANOTUBE BLOCKS	JP 6114487	8-Aug-2007
METHODS FOR CONTROLLING DENSITY POROSITY AND/OR GAP SIZE WITHIN NANOTUBE FABRIC LAYERS AND FILMS	JP 5896922	14-Feb-2011
METHODS OF USING PRE-FORMED NANOTUBES TO MAKE CARBON NANOTUBE FILMS LAYERS FABRICS RIBBONS ELEMENTS AND ARTICLES	JP 5878679	13-Jan-2003
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	JP 5781718	26-May-2005
MEMORY ARRAYS USING NANOTUBE ARTICLES WITH REPROGRAMMABLE RESISTANCE	JP 5701481	9-May-2006
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	JP 5410974	8-Aug-2007
NANOTUBE FILMS AND ARTICLES	JP 5068921	25-Jul-2002
ELECTROMECHANICAL THREE-TRACE JUNCTION DEVICES	JP 4643145	19-Dec-2002
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	HK 1138425	8-Aug-2007

NANOTUBE-BASED SWITCHING ELEMENTS WITH MULTIPLE CONTROLS AND CIRCUITS MADE FROM SAME	HK 1138101	12-Aug-2004
MEMORY ELEMENTS AND CROSS POINT SWITCHES AND ARRAYS OF SAME USING NONVOLATILE NANOTUBE BLOCKS	HK 1137163	8-Aug-2007
MEMORY ARRAYS USING NANOTUBE ARTICLES WITH REPROGRAMMABLE RESISTANCE	HK 1135796	9-May-2006
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	FR 2057633	8-Aug-2007
NANOTUBE FABRIC-BASED SENSOR SYSTEM AND METHODS OF MAKING SAME	FR 1929276	6-Sep-2006
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	FR 1880420	9-May-2006
AQUEOUS CARBON NANOTUBE APPLICATOR LIQUIDS AND METHOD FOR PRODUCING APPLICATOR LIQUIDS THEREOF	FR 1825038	15-Dec-2005
INTEGRATED NANOTUBE AND FIELD EFFECT SWITCHING DEVICE	FR 1776763	26-May-2005
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	FR 1751778	26-May-2005
METHODS OF NANOTUBE FILMS AND ARTICLES	FR 1409156	25-Jul-2002
METHODS FOR READING AND PROGRAMMING 1-R RESISTIVE CHANGE ELEMENT ARRAYS	EP 3180788	20-Jan-2016

DDR COMPATIBLE MEMORY CIRCUIT ARCHITECTURE FOR RESISTIVE CHANGE ELEMENT ARRAYS	EP 3125249	29-Jul-2015
METHODS FOR READING AND PROGRAMMING 1-R RESISTIVE CHANGE ELEMENT ARRAYS	EP 3048612	20-Jan-2016
METHODS FOR CONTROLLING DENSITY, POROSITY, AND/OR GAP SIZE WITHIN NANOTUBE FABRIC LAYERS AND FILMS	EP 2534181	14-Feb-2011
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	EP 1751778	26-May-2005
SPIN-COATABLE LIQUID FOR FORMATION OF HIGH PURITY NANOTUBE FILMS	EP 1751333	26-May-2005
NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	EP 2057633	8-Aug-2007
NANOTUBE FABRIC-BASED SENSOR SYSTEM AND METHODS OF MAKING SAME	EP 1929276	6-Sep-2006
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	EP 1880420	9-May-2006
INTEGRATED NANOTUBE AND FIELD EFFECT SWITCHING DEVICE	EP 1776763	26-May-2005
DEVICES HAVING VERTICALLY-DISPOSED NANOFABRIC ARTICLES AND METHODS OF MAKING THE SAME	EP 1593164	12-Feb-2004

NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	DE 2057633	8-Aug-2007
NANOTUBE FABRIC-BASED SENSOR SYSTEM AND METHODS OF MAKING SAME	DE 1929276	6-Sep-2006
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	DE 1880420	9-May-2006
AQUEOUS CARBON NANOTUBE APPLICATOR LIQUIDS AND METHOD FOR PRODUCING APPLICATOR LIQUIDS THEREOF	DE 1825038	15-Dec-2005
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	DE 1751778	26-May-2005
METHODS OF NANOTUBE FILMS AND ARTICLES	DE 1409156	25-Jul-2002
NANOTUBE FILMS AND ARTICLES	CN CN1556996	25-Jul-2002
METHOD FOR DYNAMICALLY ACCESSING AND PROGRAMMING RESISTIVE CHANGE ELEMENT ARRAYS	CN CN107004435	10-Aug-2015
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	CN CN102176456	9-May-2006
MEMORY ARRAYS USING NANOTUBE ARTICLES WITH REPROGRAMMABLE RESISTANCE	CN CN101484997	9-May-2006
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	CN CN101015025	26-May-2005

NONVOLATILE NANOTUBE DIODES AND NONVOLATILE NANOTUBE BLOCKS AND SYSTEMS USING SAME AND METHODS OF MAKING SAME	CN 200780037370	8-Aug-2007
NONVOLATILE RESISTIVE MEMORIES LATCH CIRCUITS AND OPERATION CIRCUITS HAVING SCALABLE TWO-TERMINAL NANOTUBE SWITCHES	CN 200780035884	8-Aug-2007
MEMORY ELEMENTS AND CROSS POINT SWITCHES AND ARRAYS OF SAME USING NONVOLATILE NANOTUBE BLOCKS	CN 200780035300	8-Aug-2007
NON-VOLATILE SHADOW LATCH USING A NANOTUBE SWITCH	CN 200680024940	9-May-2006
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	CN 200680024939.5	9-May-2006
METHODS FOR CONTROLLING DENSITY POROSITY AND/OR GAP SIZE WITHIN NANOTUBE FABRIC LAYERS AND FILMS	CN 102834418	14-Feb-2011
NRAM NONSUSPENDED REVERSIBLE NANOSWITCH NANOTUBE ARRAY	CN 102280139	9-May-2006
NANOTUBE FABRIC-BASED SENSOR SYSTEM AND METHODS OF MAKING SAME	CA 2621103	6-Sep-2006
MEMORY ARRAYS USING NANOTUBE ARTICLES WITH REPROGRAMMABLE RESISTANCE	CA 2608106	9-May-2006
TWO-TERMINAL NANOTUBE DEVICES AND SYSTEMS AND METHODS OF MAKING SAME	CA 2608056	9-May-2006
RESISTIVE ELEMENTS USING CARBON NANOTUBES	CA 2581058	20-Sep-2005

NANOTUBE-BASED TRANSFER DEVICES AND RELATED CIRCUITS	CA 2570304	26-May-2005
SPIN-COATABLE LIQUID FOR USE IN ELECTRONIC FABRICATION PROCESSES	CA 2569438	26-May-2005
METHODS OF NANOTUBE FILMS AND ARTICLES, FILMS ET ARTICLES DE NANOTUBES ET PROCEDES ASSOCIES	CA 2454895	25-Jul-2002
NANOTUBE FILMS AND ARTICLES CARBON NANOTUBE RESONATORS	CA 2454845 AU 2006287641	25-Jul-2002 5-Sep-2006
METHOD AND SYSTEM OF USING NANOTUBE FABRICS AS JOULE HEATING ELEMENTS FOR MEMORIES AND OTHER APPLICATIONS	AU 2006287609	6-Sep-2006
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METHODS FOR ACCESSING 1-R RESISTIVE CHANGE ELEMENT ARRAYS	US 2020-0219564	6-Jan-2020
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A NANOTUBE APPLICATION DEPOSITION SYSTEM FOR FORMING LOW DEFECT NANOTUBE FABRICS	US 20170246561	15-May-2017
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DDR COMPATIBLE MEMORY CIRCUIT ARCHITECTURE FOR RESISTIVE CHANGE ELEMENT ARRAYS	KR 10-2017-0015203	29-Jul-2015
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METHODS FOR PROGRAMING DDR COMPATIBLE OPEN ARCHITECTURE	US 17/007,735	31-Aug-2020
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EXHIBIT C

Trademarks

<u>Description</u>	<u>Registration/ Application Number</u>	<u>Registration/ Application Date</u>
ENRAM (CN)	878496	04-Apr-2017
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NTSL (TW)	1904639	01-Apr-2018
NTSL (US)	5377794	16-Jan-2018

EXHIBIT D

Mask Works

Description

Registration/
Application
Number

Registration/
Application
Date

None

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